

**AMENDMENTS TO THE CLAIMS:**

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

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1. (Currently amended) A semiconductor laser device comprising:  
  
a stem having a mounting surface;  
  
a first semiconductor laser element ~~directly or indirectly~~ mounted on ~~onto~~ the mounting surface of said stem, said first semiconductor laser element having an emission wavelength and a temperature dependence; and  
  
a second semiconductor laser element disposed on top of said first semiconductor laser element, said second semiconductor laser element having an emission wavelength different from the emission wavelength of said first semiconductor laser element and a temperature dependence lower than the temperature dependence of said first semiconductor laser element.
  
2. (Original) The semiconductor laser device according to claim 1, wherein the emission wavelength of said first semiconductor laser element is within a wavelength range of 640-660 nm, while the emission wavelength of said second semiconductor laser element is within a wavelength range of 770-800 nm.
  
3. (Original) The semiconductor laser device according to claim 1, wherein said second semiconductor laser element provided on top of the first semiconductor laser

element is smaller in size than said first semiconductor laser element such that a part of a top surface of said first semiconductor laser element is exposed.

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4. (Original) The semiconductor laser device according to claim 1, wherein each of said first and second semiconductor laser elements has an N-layer and a P-layer, and either the N-layers or the P-layers of said first and second semiconductor laser elements are adjacent to each other.

5. (Original) The semiconductor laser device according to claim 1, wherein each of said first and second semiconductor laser elements has an emission point and the emission points of said first and second semiconductor laser elements are located at an interval of 160 micrometers or less.

6. (Original) The semiconductor laser device according to claim 1, wherein there are a plurality of joined portions in which different soldering materials having different melting points are used.

7. (Currently amended) A semiconductor laser device comprising:  
a stem having a mounting surface; and  
a plurality of semiconductor laser elements disposed one on top of another and over directly or indirectly mounted onto the mounting surface of the stem so as to be

supported by the stem, said plurality of semiconductor laser elements having different emission wavelengths and different temperature dependencies;

wherein said plurality of semiconductor laser elements are stacked in order of temperature dependence such that the laser chip farther from the mounting surface of the stem has a lower temperature dependence than the laser chip closer to the mounting surface of the stem.

8. (Previously presented) The laser device of claim 1, wherein the second laser element emits a higher wavelength than does the first laser element that is closer to the mounting surface of the stem.

9. (Previously presented) The laser device of claim 7, wherein the laser chip farther from the mounting surface emits a higher wavelength than does the laser chip closer to the mounting surface of the stem.

10. (Currently amended) A semiconductor laser device comprising:  
a first semiconductor laser element supported by a mount, said first semiconductor laser element having an emission wavelength and a temperature dependence; and  
a second semiconductor laser element disposed at least partially over said first semiconductor laser element ~~and also supported by the mount~~, said second semiconductor laser element having an emission wavelength higher than the emission wavelength of said

first semiconductor laser element and a temperature dependence lower than the temperature dependence of said first semiconductor laser element so that power of the second semiconductor laser element is less affected by a given change in temperature than power of the first semiconductor laser element which is closer to the mount.

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11. (Currently amended) A semiconductor laser device comprising:

a stem including a mounting surface;

a first semiconductor laser element ~~directly or indirectly~~ mounted on the mounting surface of said stem, said first semiconductor laser element having an emission wavelength in a range of 640-660 nm; and

a second semiconductor laser element disposed on top of said first semiconductor laser element and having an emission wavelength in a range of 770-800 nm.

12. (Previously presented) The semiconductor laser device of claim 11, wherein said second semiconductor laser element has a temperature dependence lower than a temperature dependence of said first semiconductor laser element so that power of the second semiconductor laser element is less affected by a given change in temperature than power of the first semiconductor laser element which is closer to the stem.

13. (New) The semiconductor laser device of claim 11, wherein the first semiconductor laser element is directly mounted on the mounting surface of said stem.

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14. (New) The semiconductor laser device of claim 1, wherein the first semiconductor laser element is directly mounted on the mounting surface of said stem.

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